

**IN THE SPECIFICATION**

On page 5, line 6, change "FIG. 3" to -- FIG. 3A --; and

On page 7, line 14, change "downstream" to -- downstream --.

**IN THE CLAIMS**

Please amend the claims as follows:

Sub B1  
A1

1. (Amended) A shallow trench isolation in a substrate, said shallow trench isolation structure comprising:

- a trench in said substrate; and
- a nitride liner recessed within said trench and the nitride liner forming a partially enclosed volume, said partially enclosed volume being completely filled with a dielectric material which also completely fills the trench, such that an uppermost surface of said nitride liner is disposed below a transistor channel depth [representing a width] of a transistor disposed in a well beside said shallow trench isolation structure.

Sub C2  
A2

8. (Amended) A shallow trench isolation in a substrate, said shallow trench isolation structure comprising:

- a trench in the substrate;
- a nitride liner recessed within said trench; and
- an oxide fill disposed above said nitride liner, such that said oxide fill extends above and below an uppermost surface of said nitride liner substantially to a top surface of said substrate and completely filling below the uppermost surface, respectively.